



Product Overview

NTMS4802N: Power MOSFET 30V 18A 4 mOhm Single N-Channel SO-8

For complete documentation, see the data sheet

Product Description

Power MOSFET 30V 18A 4 mOhm Single N-Channel SO-8

Features

- Low $R_{DS(on)/sub}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- This is a PbFree Device

Applications

- DCDC Converters
- Synchronous MOSFET
- Printers

Part Electrical Specifications

Product	Compliance	Status	Channel Polarity	Configuration	$V_{DS(sat)}$ Min (V)	V_{GS} Max (V)	$V_{GS(th)}$ Max (V)	I_D Max (A)	P_D Max (W)	$r_{DS(on)}$ Max @ $V_{GS} = 2.5V$ (m)	$r_{DS(on)}$ Max @ $V_{GS} = 4.5V$ (m)	$r_{DS(on)}$ Max @ $V_{GS} = 10V$ (m)	Q_g Typ @ $V_{GS} = 4.5V$ (nC)	Q_g Typ @ $V_{GS} = 10V$ (nC)	Q_{gd} Typ @ $V_{GS} = 4.5V$ (nC)	Q_{rr} Typ (nC)	C_{iss} Typ (pF)	C_{oss} Typ (pF)	C_{rss} Typ (pF)	Package Type
NTMS4802NR2G	Pb-free Halide free	Active	N-Channel	Single	30	20	2.5	18	2.5		5.5	4	36	75	13	40	5300	880	460	SOIC-8

For more information please contact your local sales support at www.onsemi.com

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